

TOSHIBA PHOTO COUPLER GaAs IRED & PHOTO-TRIAC

TLP666G

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVER
SOLID STATE RELAY

The TOSHIBA TLP666G consists of a zero voltage crossing turn-on photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

- Peak Off-State Voltage : 400V (Min.)
- Trigger LED Current : 10mA (Max.)
- On-State Current : 100mA (Max.)
- UL Recognized : UL1577, File No. E67349
- Isolation Voltage : 5000V_{rms} (Min.)
- Option (D4) type
VDE Approved : DIN VDE0884 / 08.87,
Certificate No. 68383

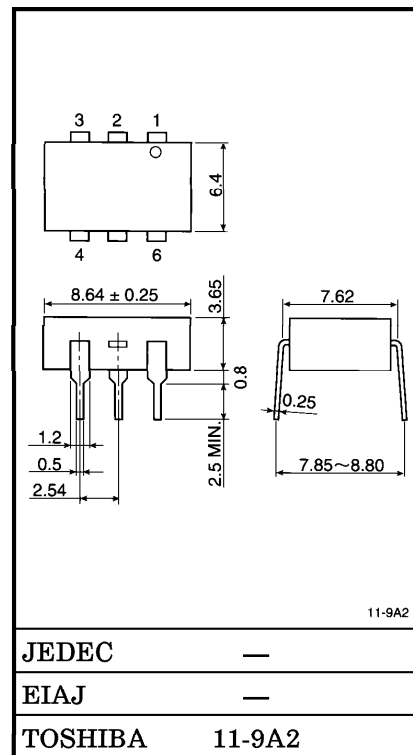
Maximum Operating Insulation Voltage : 630V_{PK}

Highest Permissible Over Voltage : 6000V_{PK}

(Note 1) When a VDE0884 approved type is needed,
please designate the "Option (D4)"

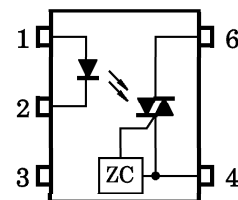
- Structural Parameter
 - Creepage Distance : 7.0mm (Min.)
 - Clearance : 7.0mm (Min.)
 - Insulation Thickness : 0.5mm (Min.)

Unit in mm



Weight : 0.44g

PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : TERMINAL 1
- 6 : TERMINAL 2

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC			SYMBOL	RATING	UNIT
LED	Forward Current		I _F	50	mA
	Forward Current Derating (Ta≥53°C)		ΔI _F /°C	−0.7	mA/°C
	Peak Forward Current (100μs pulse, 100pps)		I _{FP}	1	A
	Reverse Voltage		V _R	5	V
	Junction Temperature		T _j	125	°C
DETECTOR	Off-State Output Terminal Voltage		V _{DRM}	400	V
	On-State RMS Current	Ta=25°C	I _T (RMS)	100	mA
		Ta=70°C		50	
	On-State Current Derating (Ta≥25°C)		ΔI _T /°C	−1.1	mA/°C
	Peak On-State Current (100μs pulse, 120pps)		I _{TP}	2	A
	Peak Nonrepetitive Surge Current (P _W =10ms, DC=10%)		I _{TSM}	1.2	A
	Junction Temperature		T _j	115	°C
	Storage Temperature Range		T _{stg}	−55~125	°C
	Operating Temperature Range		T _{opr}	−40~100	°C
	Lead Solder Temperature (10s)		T _{sold}	260	°C
Isolation Voltage (AC, 1min., R.H.≤60%) (Note 2)		BV _S	5000	V _{rms}	

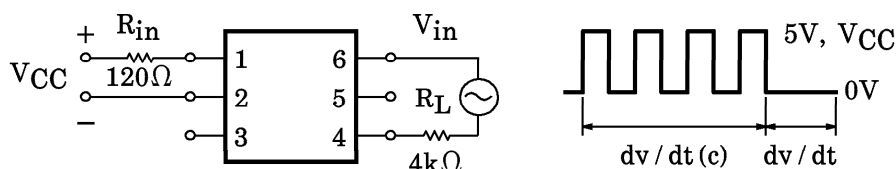
(Note 2) Pins 1, 2 and 3 shorted together and pins 4 and 6 shorted together.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{AC}	—	—	120	V _{ac}
Forward Current	I _F	15	20	25	mA
Peak On-State Current	I _{TP}	—	—	1	A
Operating Temperature	T _{opr}	−25	—	85	°C

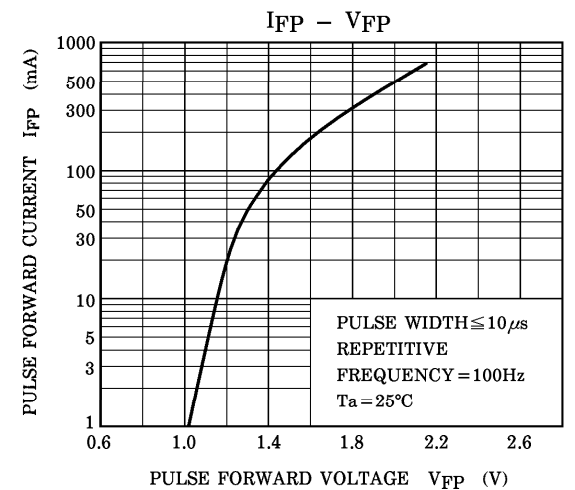
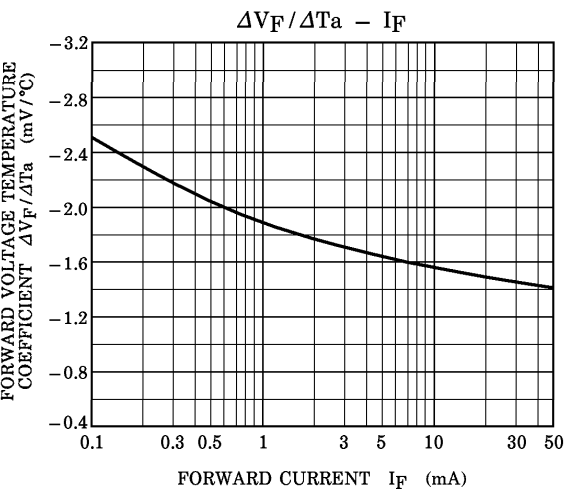
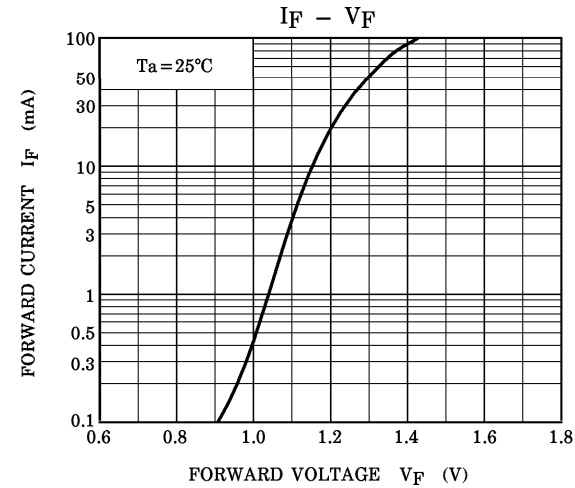
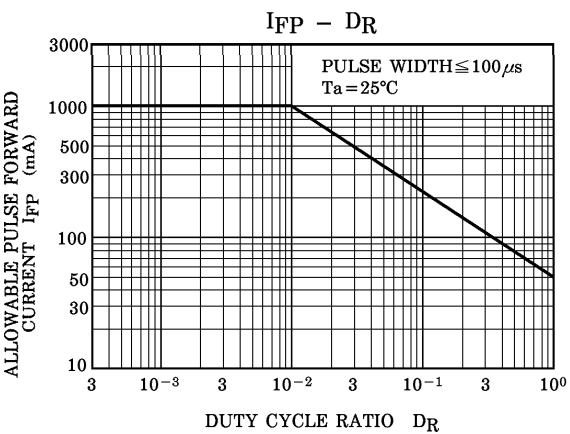
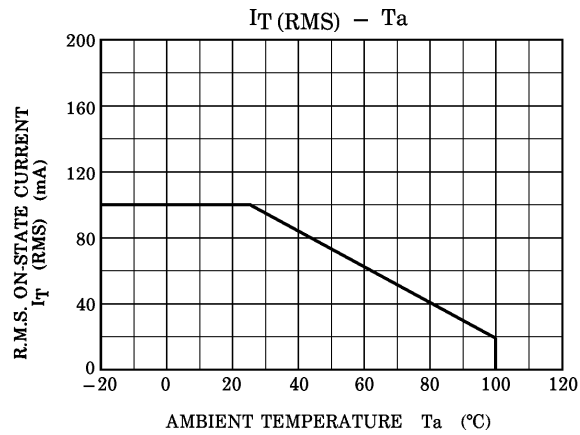
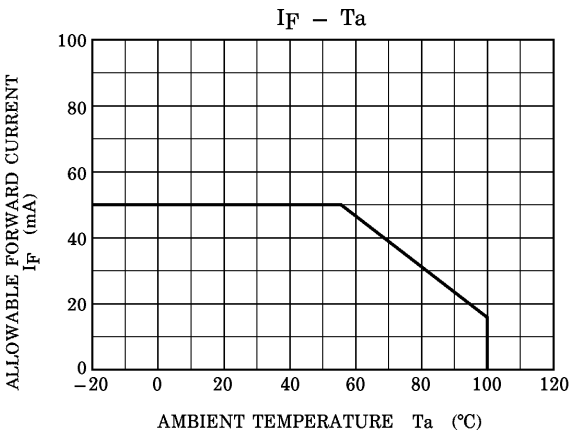
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

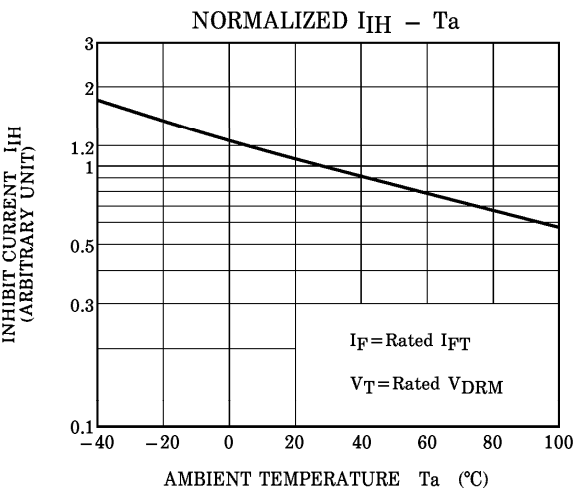
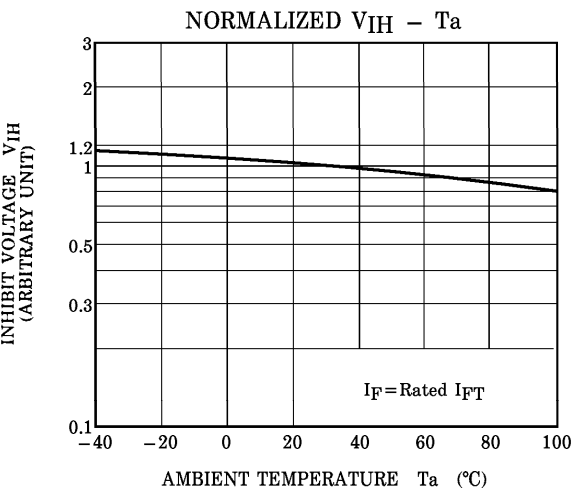
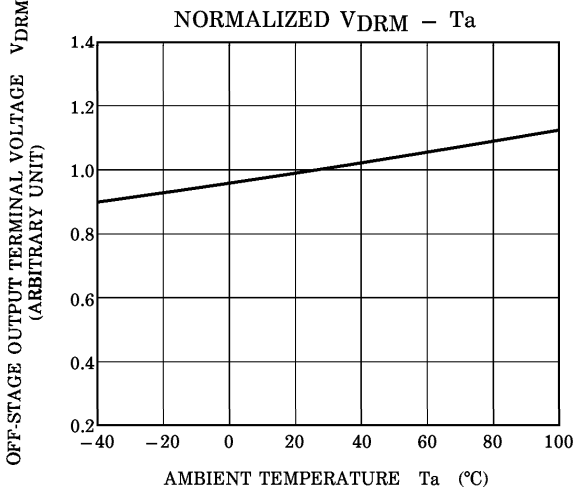
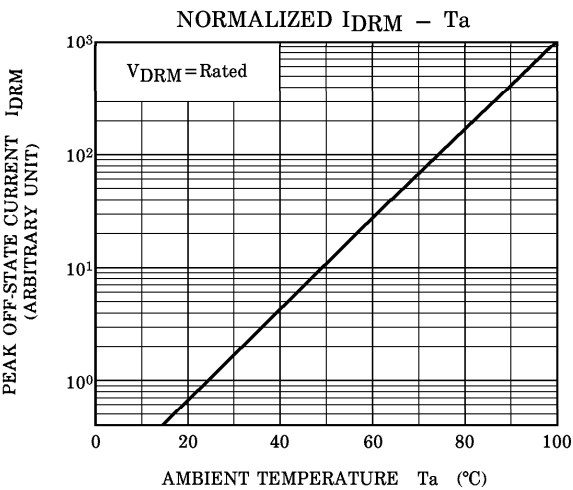
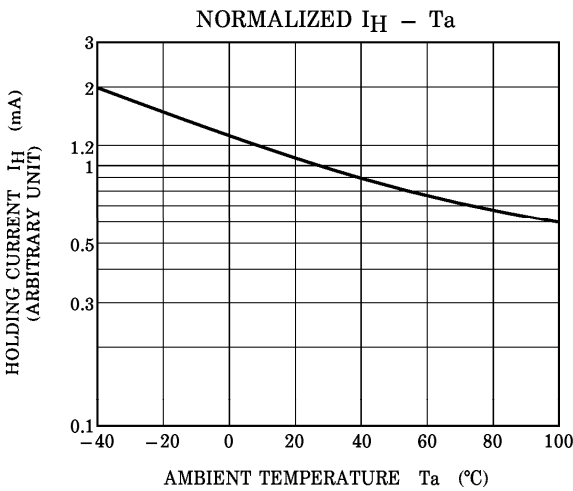
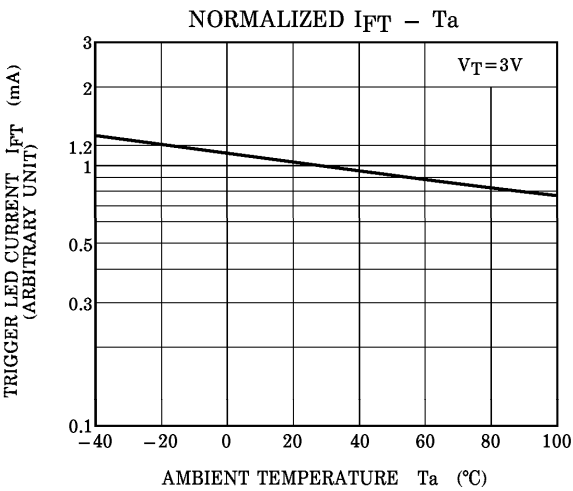
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Peak Off-State Current	I_{DRM}	$V_{\text{DRM}} = 400\text{V}$	—	10	100	nA
	Peak On-State Voltage	V_{TM}	$I_{\text{TM}} = 100\text{mA}$	—	1.7	3.0	V
	Holding Current	I_H	—	—	0.6	—	mA
	Critical Rate of Rise of Off-State Voltage	dv/dt	$V_{\text{in}} = 120V_{\text{rms}}, T_a = 85^\circ\text{C}$ (Note 3)	200	500	—	$\text{V} / \mu\text{s}$
	Critical Rate of Rise of Commutating Voltage	$dv/dt(c)$	$V_{\text{in}} = 30V_{\text{rms}}, I_T = 15\text{mA}$ (Note 3)	—	0.2	—	$\text{V} / \mu\text{s}$

(Note 3) dv/dt TEST CIRCUIT

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I_{FT}	$V_T = 3\text{V}$	—	5	10	mA
Inhibit Voltage	V_{IH}	$I_F = \text{Rated } I_{\text{FT}}$	—	—	40	V
Leakage in Inhibited State	I_{IH}	$I_F = \text{Rated } I_{\text{FT}}$ $V_T = \text{Rated } V_{\text{DRM}}$	—	100	300	μA
Capacitance (Input to Output)	C_S	$V_S = 0, f = 1\text{MHz}$	—	0.8	—	pF
Isolation Resistance	R_S	$V_S = 500\text{V}, \text{R.H.} \leq 60\%$	5×10^{12}	10^{14}	—	Ω
Isolation Voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	Vdc





RESTRICTIONS ON PRODUCT USE

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